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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/450,912	11/29/1999	BRIAN JOSEPH MCNAMARA	17481	8320
75	90 07/14/2004		EXAM	INER
THE WHITAKER CORPORATION 4550 NEW LINDEN HILL ROAD STE 450			SMITH, SHEILA B	
WILMINGTON		J	ART UNIT	PAPER NUMBER
			2681	1
			DATE MAILED: 07/14/200	4 <i>V</i>

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
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Office Action Summary	09/450,912 Examiner	MCNAMARA, BRIAN JOSEPH			
		Art Unit			
The MAILING DATE of this communication a	Sheila B. Smith	2681			
Period for Reply	ippears on the cover sheet w	Tur the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a r - If NO period for reply is specified above, the maximum statutory perion - Failure to reply within the set or extended period for reply will, by state that the period for reply will be period for reply will, by state that the period for reply will, by state that the period for reply will be period for reply wi	N. 1.136(a). In no event, however, may a reply within the statutory minimum of this od will apply and will expire SIX (6) MO tute, cause the application to become A	reply be timely filed rty (30) days will be considered timely. NTHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).			
Status					
1) Responsive to communication(s) filed on 29	April 2004.				
	his action is non-final.				
	,—				
closed in accordance with the practice unde	r <i>Ex parte Quayle</i> , 1935 C.I). 11, 453 O.G. 213.			
Disposition of Claims					
4) ☐ Claim(s) 1-21 is/are pending in the application 4a) Of the above claim(s) is/are withd 5) ☐ Claim(s) 9-15 and 19-21 is/are allowed. 6) ☐ Claim(s) 1-7 and 16-18 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	rawn from consideration.				
Application Papers					
9) The specification is objected to by the Exami					
10)☐ The drawing(s) filed on is/are: a)☐ a		•			
Applicant may not request that any objection to the					
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the					
Priority under 35 U.S.C. § 119					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a li	ents have been received. ents have been received in A riority documents have beer eau (PCT Rule 17.2(a)).	Application No received in this National Stage			
Attachment(s)	·				
1) Notice of References Cited (PTO-892)	4) Interview	Summary (PTO-413)			
 Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date 		s)/Mail Date nformal Patent Application (PTO-152) 			

Application/Control Number: 09/450,912

Art Unit: 2681

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

1. Claims 1-7, are rejected under 35 U.S.C. 102(e) as being anticipated by Yeh (U. S. Patent Number 5,995,814).

Regarding claim 1, Yeh discloses essentially all the claimed invention as set fourth in the instant application, further Yeh discloses single stage dual-band low-noise amplifier for use in a wireless communication system receiver. In addition Yeh discloses a first impedance element (L1) and a second impedance element (L2) between an RF input port (IN) and an RF output port (OUT) (as exhibited in figure 1), the tuning circuit being tuned by the first and second impedance elements (L1, L2) to receive a first RF signal and to provide the first RF signal at the output port, the tuning circuit being tuned by the first impedance element alone (which reads on subset) to receive a second RF signal and to provide the second RF signal at the output port (which reads on column 10 lines 21-25), a switching transistor (Q1)being switched on and off by changing its bias voltage, a band control voltage source (V1, V2) connected to the switching transistor to change its bias voltage, and the switching transistor (Q1) having conducting gates (emitter) connected to the second impedance element (L2) to short the second impedance

Art Unit: 2681

element, which tunes the tuning circuit by the first impedance element (L1) (which reads on column 4 lines 32-35).

Regarding claim 2, Yeh discloses a first and second impedance elements are inductance impedance elements (L1, L2).

Regarding claims 3 and 7, Yeh discloses a first and second impedance elements are capacitance impedance elements (C1, C3).

Regarding claim 4, Yeh discloses a conducting drain and source nodes of the switching transistor (Q1) being in parallel connection with the second impedance element (L2) to open circuit the second impedance element.

Regarding claim 5, Yeh discloses a first and second impedance elements are inductance impedance elements (L1, L2).

Regarding claim 6, Yeh discloses a resistance (R1) connected across the conducting gates of the switching transistor (Q1), the source of band control voltage (V1, V2) being connected to a dividing point of the resistance, and the conducting drain and source nodes of the switching transistor (Q1) being is series connection with the second impedance element (L2) to open-circuit the second impedance element (as exhibited in figure 5).

Application/Control Number: 09/450,912 Page 4

Art Unit: 2681

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

2. Claims 16-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yeh.

Regarding claim 16, Yeh discloses the circuit of claim 1 as described above. Yeh, however, fails to disclose the use of a MESFET transistor.

Official notice is taken that the use of a MESFET transistor for a switching transistor is well know in the art. Therefore, it would have been obvious to a person of ordinary skill in the art to use any well know transistor, including the well known MESFET transistor to implement the required switching circuitry in Yeh for the purpose of providing low distortion power application.

Regarding claims 17 and 18, Yeh discloses a switching transistor (Q1) is integrally formed with the tuning circuit in a single integrated circuit (which reads on column 4 lines 32-35).

Allowable Subject Matter

3. Claim 8 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Application/Control Number: 09/450,912 Page 5

Art Unit: 2681

4. Claims 9-15,19-21 allowed.

Claim 9 is allowed. The following is an examiner's statement of reasons for allowance: The prior art of record considered alone or in combination neither anticipates nor renders a dual band RF circuit with a first impedance element and a second impedance element between an RF input port and an RF output port, the tuning circuit being tuned by the first and second impedance elements to receive a first RF signal and to provide the first RF signal at the output port, the tuning circuit being tuned by the first impedance element alone to receive a second RF signal and to provide the second RF signal at the output port, a switching transistor being switched on and off by changing its bias voltage, the second switching transistor having conducting drain and source nodes connected to the second the second capacitance impedance element, which tunes the tuning circuit by the first capacitance impedance element.

The prior art of record provided numerous teachings of a dual band RF circuit with a first impedance element and a second impedance element between an RF input port and an RF output port. However, the prior art of record failed to specifically disclose the second switching transistor having conducting drain and source nodes connected to the second the second capacitance impedance element, which tunes the tuning circuit by the first capacitance impedance element.

5. Regarding claims 10-15,19-21, are allowed as being dependent upon independent base claims that have been allowed.

Response to Arguments

6. Applicant's arguments filed 4/29/04 have been fully considered but they are not persuasive.

Art Unit: 2681

Regarding applicants arguments concerning there being no switching transistor disclosed in Yeh, the examiner disagrees Yeh, discloses at column 4 lines 32-37, "the capacitor C3 serves as a bypass capacitor, to shunt the emitter of Q1 to ground potential at RF frequencies such that the emitter biasing resistor R1 will not degrade the high-frequency transistor gain", the examiner contends that this section reads on switching because shunting the emitter the signal takes a different path which reads on switching.

Conclusion

7. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Sheila B. Smith whose telephone number is (703)305-0104. The examiner can normally be reached on Monday-Thursday 6:00 am - 3:00 pm.

Application/Control Number: 09/450,912 Page 7

Art Unit: 2681

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Erika Gary can be reached on 703-308-0123. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

S. Smith 5-5-July 11, 2004

SINH TRAN PRIMARY EXAMINER